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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

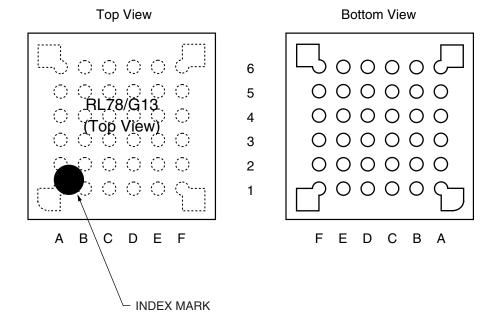
-	
Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101gfafb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

#### 1.3.6 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	Α	В	С	D	E	F	
6	P60/SCLA0	V <sub>DD</sub>	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62	P61/SDAA0	Vss	REGC	RESET	P120/ANI19	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AV <sub>REFP</sub>	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/Tl02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (T007)	P147/ANI18	P25/ANI5	1
	Α	В	С	D	F	F	

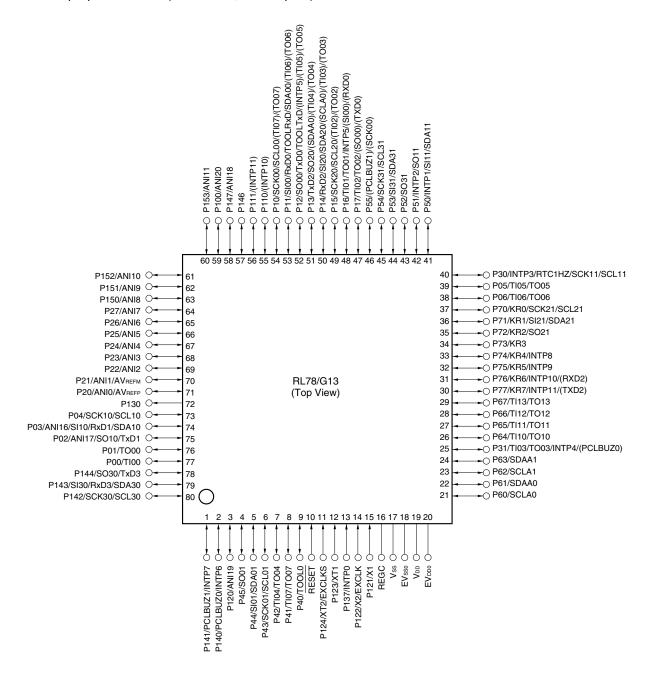
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

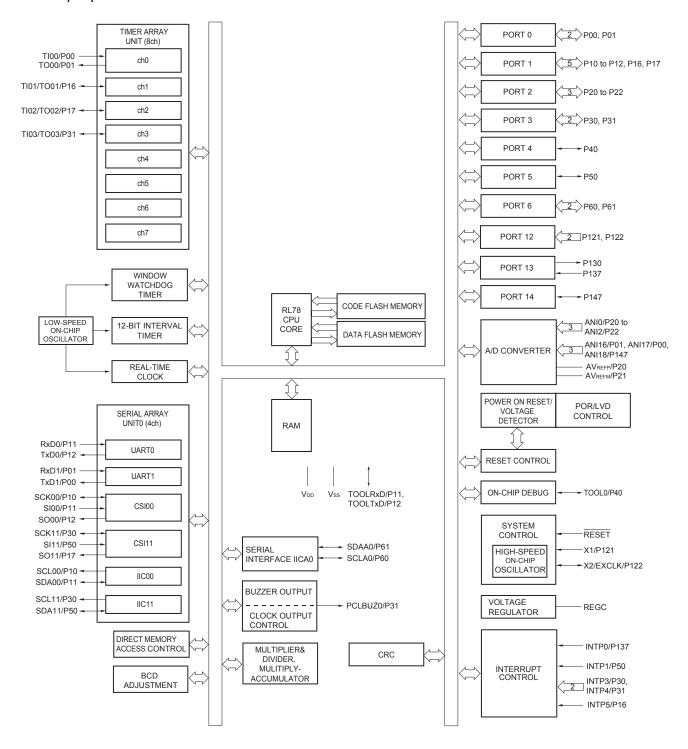
#### 1.3.12 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 x 12 mm, 0.5 mm pitch)

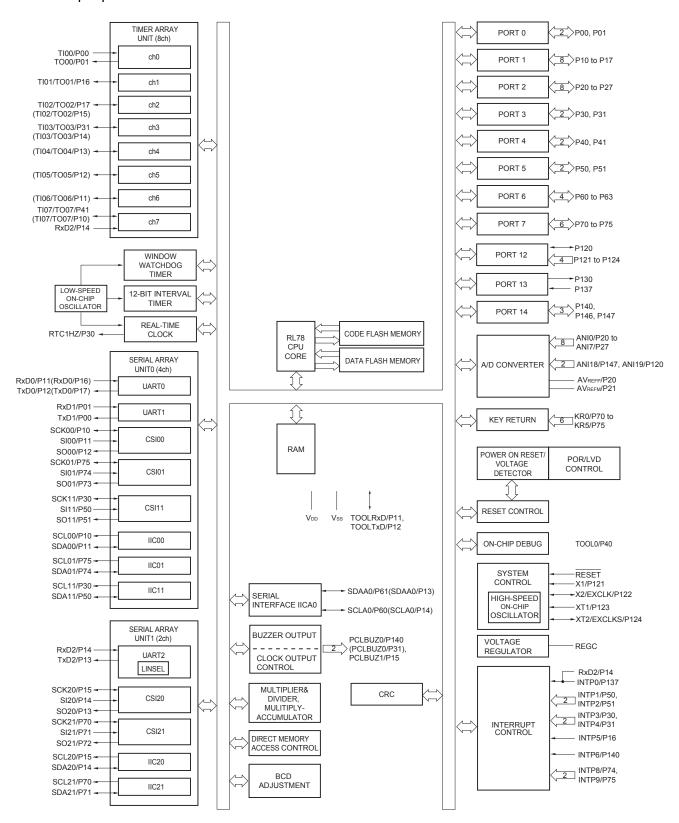


- Cautions 1. Make EVsso pin the same potential as Vss pin.
  - 2. Make VDD pin the potential that is higher than EVDDO pin.
  - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
  - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V<sub>DD</sub> and EV<sub>DD0</sub> pins and connect the Vss and EV<sub>SS0</sub> pins to separate ground lines.
  - **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register** (**PIOR**) in the RL78/G13 User's Manual.

### 1.5.3 25-pin products



### 1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

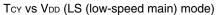
- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVSSO, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
  - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
  - 3. When high-speed system clock and subsystem clock are stopped.
  - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
  - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

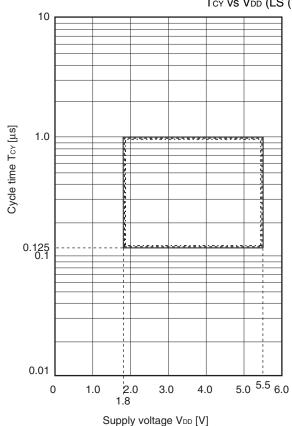
HS (high-speed main) mode: 2.7 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 16 MHz

LS (low-speed main) mode:  $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$  to 8 MHz LV (low-voltage main) mode:  $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$  to 4 MHz

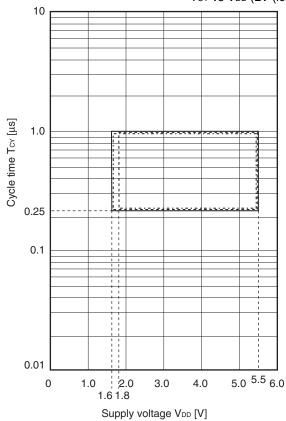
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
  - 2. fin: High-speed on-chip oscillator clock frequency
  - **3.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
  - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C





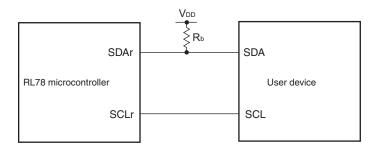
- When the high-speed on-chip oscillator clock is selected
- During self programming
   When high-speed system clock is selected

### Tcy vs Vdd (LV (low-voltage main) mode)

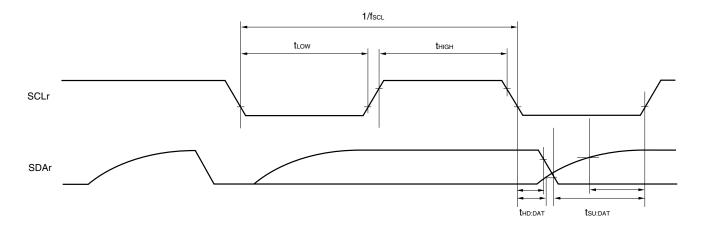


- When the high-speed on-chip oscillator clock is selected During self programming
- --- When high-speed system clock is selected

## Simplified I<sup>2</sup>C mode mode connection diagram (during communication at same potential)



#### Simplified I<sup>2</sup>C mode serial transfer timing (during communication at same potential)



- **Remarks 1.** R<sub>b</sub>[Ω]:Communication line (SDAr) pull-up resistance, C<sub>b</sub>[F]: Communication line (SDAr, SCLr) load capacitance
  - 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
  - fmck: Serial array unit operation clock frequency
     (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
    - n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V  $\leq$  EV<sub>DD0</sub> < 4.0 V and 2.3 V  $\leq$  V<sub>b</sub>  $\leq$  2.7 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- \* This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with  $EV_{DD0} \ge V_b$ .
- **6.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V  $\leq$  EV<sub>DD0</sub> < 3.3 V and 1.6 V  $\leq$  V<sub>b</sub>  $\leq$  2.0 V

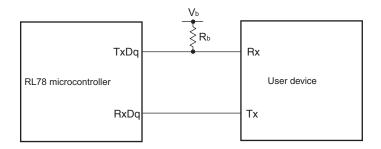
Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = 
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- \* This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

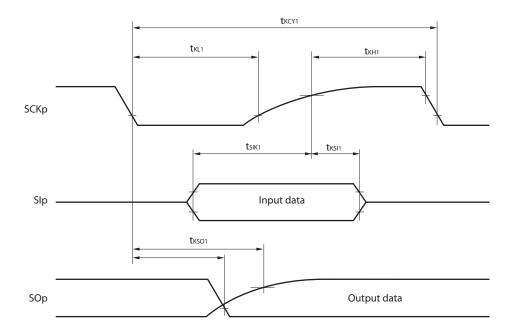
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

**UART** mode connection diagram (during communication at different potential)

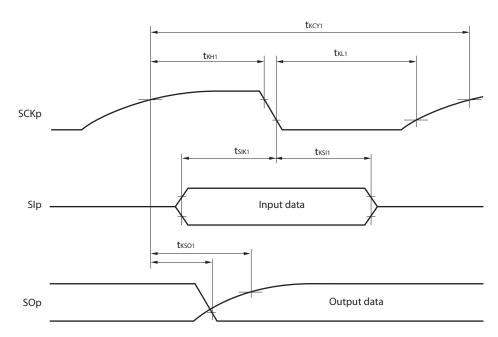




# CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



## CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

### 2.5.2 Serial interface IICA

### (1) I2C standard mode

(Ta = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	С	Conditions	, ,	h-speed Mode	,	v-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
		mode:	1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	0	100	0	100	0	100	kHz
		fc∟k≥ 1 MHz	1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_	_	0	100	0	100	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
condition		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	_	_	4.7		4.7		μS
Hold time <sup>Note 1</sup>	thd:STA	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	_	_	4.0		4.0		μS
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
" <u>L</u> "		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	_	_	4.7		4.7		μS
Hold time when SCLA0 =	tніgн	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
"H"		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	_	_	4.0		4.0		μS
Data setup time	tsu:dat	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	250		250		250		ns
(reception)		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	250		250		250		ns
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	250		250		250		ns
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	-	_	250		250		ns
Data hold time	thd:dat	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
(transmission)Note 2		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	_	_	0	3.45	0	3.45	μS
Setup time of stop	tsu:sto	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
condition		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	-	_	4.0		4.0		μS
Bus-free time	<b>t</b> BUF	2.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.8 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV <sub>DD0</sub> :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV <sub>DD0</sub> ≤	≤ 5.5 V	_	_	4.7		4.7		μS

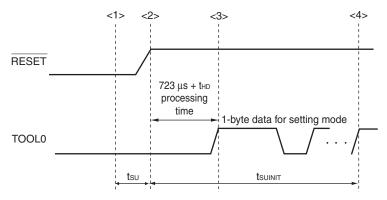
(Notes, Caution and Remark are listed on the next page.)



#### 2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuіліт	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

**Remark** tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (2/5)$ 

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low <sup>Note 1</sup>	lo <sub>L1</sub>	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
		P40 to P47, P102 to P106, P120,	$2.7~V \leq EV_{DD0} < 4.0~V$			15.0	mA
			$2.4~\text{V} \leq \text{EV}_{\text{DD0}} < 2.7~\text{V}$			9.0	mA
		Total of P05, P06, P10 to P17, P30,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			40.0	mA
		P31, P50 to P57, P60 to P67,	$2.7~V \leq EV_{DD0} < 4.0~V$			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 $(\text{When duty} \leq 70\%^{\text{Note 3}})$	2,4 V ≤ EV <sub>DD0</sub> < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				80.0	mA
	lo <sub>L2</sub>	Per pin for P20 to P27, P150 to P156			_	0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	$2,4~V \leq V_{DD} \leq 5.5~V$	_		5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
  - 2. Do not exceed the total current value.
  - **3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins =  $(lol \times 0.7)/(n \times 0.01)$ 

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$ 

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

## (2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions		ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	500		ns
SCKp high-/low-level width	<b>t</b> кн1,	4.0 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	tkcy1/2 - 24		ns
	t <sub>KL1</sub>	2.7 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	tkcy1/2 - 36		ns
		2.4 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	4.0 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	66		ns
		2.7 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	66		ns
		2.4 V ≤ EV <sub>DD</sub>	<sub>00</sub> ≤ 5.5 V	113		ns
SIp hold time (from SCKp↑) Note 2	<b>t</b> KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	o 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
  - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3).
  - g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
  - 2. fmck: Serial array unit operation clock frequency
    - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
    - n: Channel number (mn = 00 to 03, 10 to 13))

#### (4) During communication at same potential (simplified I<sup>2</sup>C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	HS (high-sp Mo	,	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$		400 Note1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$		100 Note1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1/fмск + 220		ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$	Note2		
		$2.4~V \leq EV_{DD} \leq 5.5~V,$	1/fмск + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	0	770	ns
		$C_b = 50$ pF, $R_b = 2.7$ k $\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			

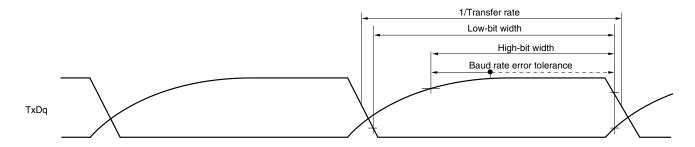
Notes 1. The value must also be equal to or less than fmck/4.

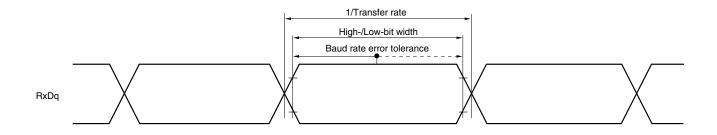
2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V<sub>DD</sub> tolerance (for the 20- to 52-pin products)/EV<sub>DD</sub> tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

#### UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \textbf{Remarks 1.} & R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ & C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$ 
  - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
  - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
  - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

# (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

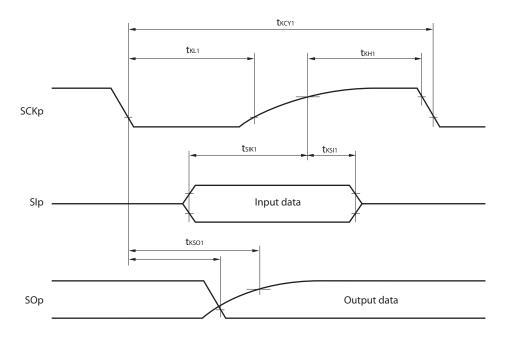
 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$ 

Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0$ $V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$	600		ns
			$2.7~V \leq EV_{DD0} < 4.0~V,~2.3~V \leq V_b \leq 2.7$ $V,$ $C_b = 30~pF,~R_b = 2.7~k\Omega$	1000		ns
			$2.4~V \leq EV_{DD0} < 3.3~V,~1.6~V \leq V_b \leq 2.0$ $V,$ $C_b = 30~pF,~R_b = 5.5~k\Omega$	2300		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$_{0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$ $R_{b} = 1.4 \text{ k}\Omega$	tксу1/2 - 150		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$_{0}<4.0$ V, 2.3 V $\leq$ V $_{b}\leq$ 2.7 V, $R_{b}=2.7$ k $\Omega$	tkcy1/2 - 340		ns
		$2.4 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$_{0} < 3.3 \ V, \ 1.6 \ V \leq V_{b} \leq 2.0 \ V,$ $R_{b} = 5.5 \ k\Omega$	tkcy1/2 - 916		ns
SCKp low-level width	tĸL1	$4.0 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$_{0}$ $\leq$ 5.5 V, 2.7 V $\leq$ V $_{b}$ $\leq$ 4.0 V, $R_{b}$ = 1.4 k $\Omega$	tксу1/2 - 24		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$_{0}$ < 4.0 V, 2.3 V $\leq$ V $_{b}$ $\leq$ 2.7 V, $R_{b}$ = 2.7 k $\Omega$	tксү1/2 – 36		ns
		$2.4 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF}, \text{ F}$	$_{0}$ < 3.3 V, 1.6 V $\leq$ V $_{b}$ $\leq$ 2.0 V, $R_{b}$ = 5.5 k $\Omega$	tkcy1/2 - 100		ns

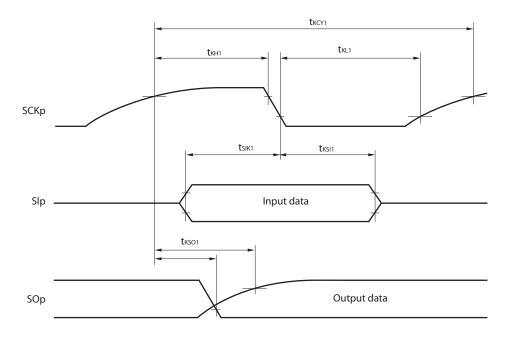
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (Vpd tolerance (for the 20- to 52-pin products)/EVpd tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

# CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



## CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remarks 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

**2.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

### 3.6 Analog Characteristics

#### 3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage					
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = V <sub>BGR</sub>				
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (–) = AVREFM				
ANI0 to ANI14	Refer to <b>3.6.1 (1)</b> .	Refer to <b>3.6.1 (3)</b> .	Refer to <b>3.6.1 (4)</b> .				
ANI16 to ANI26	Refer to <b>3.6.1 (2)</b> .						
Internal reference voltage	Refer to <b>3.6.1 (1)</b> .		-				
Temperature sensor output							
voltage							

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error <sup>Note 1</sup>	AINL	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error <sup>Notes 1, 2</sup>	Ezs	10-bit resolution AVREFP = VDD Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Full-scale error <sup>Notes 1, 2</sup>	Ers	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Integral linearity error	ILE	10-bit resolution AVREFP = VDD Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±1.5	LSB
Analog input voltage	Vain	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage output (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)			VBGR Note 4		V
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)			VTMPS25 Note	4	V

(Notes are listed on the next page.)



#### 4.8 44-pin Products

R5F100FAAFP, R5F100FCAFP, R5F100FDAFP, R5F100FEAFP, R5F100FFAFP, R5F100FGAFP,

R5F100FHAFP, R5F100FJAFP, R5F100FKAFP, R5F100FLAFP

R5F101FAAFP, R5F101FCAFP, R5F101FDAFP, R5F101FEAFP, R5F101FFAFP, R5F101FGAFP,

R5F101FHAFP, R5F101FJAFP, R5F101FKAFP, R5F101FLAFP

R5F100FADFP, R5F100FCDFP, R5F100FDDFP, R5F100FEDFP, R5F100FFDFP, R5F100FGDFP,

R5F100FHDFP, R5F100FJDFP, R5F100FKDFP, R5F100FLDFP

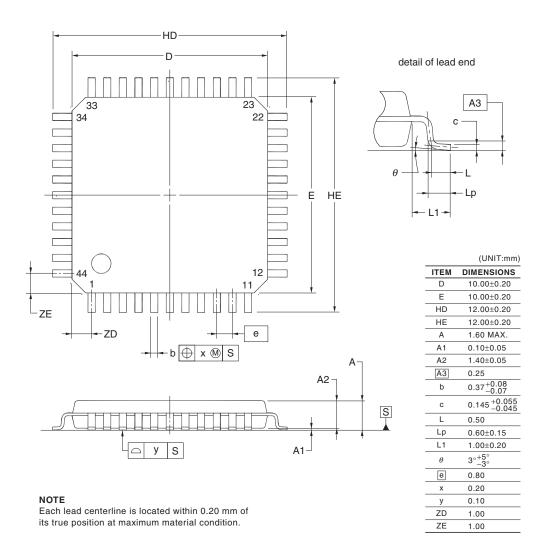
R5F101FADFP, R5F101FCDFP, R5F101FDDFP, R5F101FEDFP, R5F101FFDFP, R5F101FGDFP,

R5F101FHDFP, R5F101FJDFP, R5F101FKDFP, R5F101FLDFP

R5F100FAGFP, R5F100FCGFP, R5F100FDGFP, R5F100FEGFP, R5F100FFGFP, R5F100FGGFP,

R5F100FHGFP, R5F100FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



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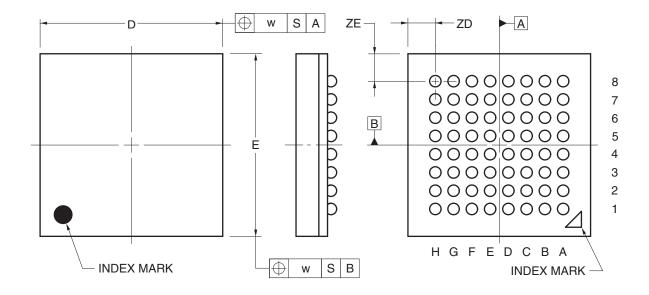


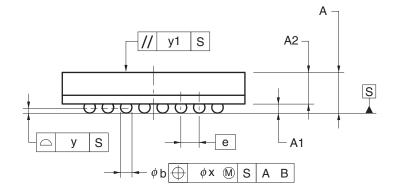
R5F100LCABG, R5F100LDABG, R5F100LEABG, R5F100LFABG, R5F100LGABG, R5F100LHABG, R5F100LJABG

R5F101LCABG, R5F101LDABG, R5F101LEABG, R5F101LFABG, R5F101LGABG, R5F101LHABG, R5F101LJABG

R5F100LCGBG, R5F100LDGBG, R5F100LEGBG, R5F100LFGBG, R5F100LGGBG, R5F100LHGBG, R5F100LJGBG

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-VFBGA64-4x4-0.40	PVBG0064LA-A	P64F1-40-AA2-2	0.03





	(UNIT:mm)
ITEM	DIMENSIONS
D	4.00±0.10
Е	4.00±0.10
W	0.15
Α	0.89±0.10
A1	0.20±0.05
A2	0.69
е	0.40
b	0.25±0.05
х	0.05
у	0.08
y1	0.20
ZD	0.60
ZE	0.60

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